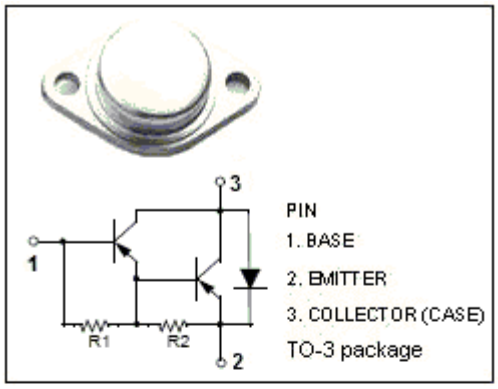
isc Silicon PNP Darlingtion Power Transistor 2N6054

DESCRIPTION

- Built-in Base-Emitter Shunt Resistors
- Low Collector-Emitter Saturation Voltage-
  : $V_{CE\ (sat)}$= -2.0V(Max.)@I_C= -4.0A
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -80V(Min)
- Complement to type 2N6056

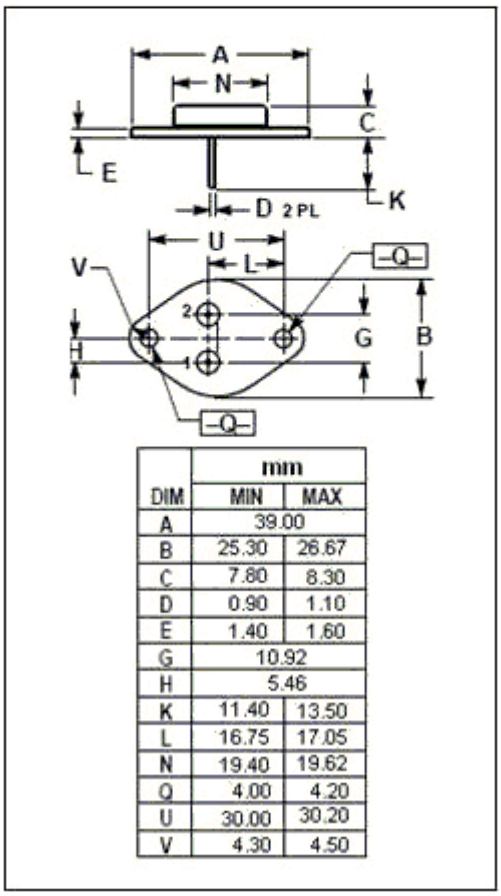


APPLICATIONS

- Designed for general purpose amplifier and low frequency switching applications.

ABSOLUTE MAXIMUM RATINGS(T_C=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-8	A
I_{CM}	Collector Current-Peak	-16	A
I_B	Base Current	-120	mA
P_C	Collector Power Dissipation@T_C=25℃	100	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature	-65~200	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	ThermalResistance, Junction to Case	1.75	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -100mA ; I_B= 0	-80		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -16mA		-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -8A; I_B= -80mA		-3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -8A; I_B= -80mA		4.0	V
$V_{BE(on)}$	Base-Emitter On voltage	I_C= -4A ; V_{CE}= -3V		-2.8	V
I_{CEO}	Collector Cutoff current	V_{CE}= -40V; I_B=0		-0.5	mA
I_{CEX}	Collector Cutoff current	V_{CE}= -80V;$V_{BE(off)}$= -1.5V V_{CE}= -80V;$V_{BE(off)}$= -1.5V,T_C=150℃		-0.5 -5.0	mA
I_{EBO}	Emitter Cut-off current	V_{EB}= -5V; I_C= 0		-2.0	mA
h_{FE-1}	DC Current Gain	I_C= -4A ; V_{CE}= -3V	750	18000	
h_{FE-2}	DC Current Gain	I_C= -8A ; V_{CE}= -3V	100		
C_{OB}	Output Capacitance	I_E=0 ; V_{CB}= -10V; f_{test}= 0.1MHz		350	pF